

AMENDMENTS TO THE CLAIMS

The claims in this listing will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1. (Currently Amended) A light-emitting device formed by depositing p-type and n-type nitride semiconductor layers, comprising:

deposited p-type and n-type nitride semiconductor layers;
semiconductor-surface-electrodes to apply currents into each of the semiconductor layers;
an insulating layer which holds the semiconductor layers, said insulating layer comprising two surfaces; and

mount-surface-electrodes being structured and arranged to mount the light-emitting device onto a mounting substrate by using solder, the mount-surface-electrodes being provided on one surface of the insulating layer which is opposite to the other surface of the insulating layer where the semiconductor-surface-electrodes are made;

wherein one of the semiconductor layers has a non-deposited area where the other semiconductor layer is not deposited;

one of the semiconductor-surface-electrodes is built up on the surface of the non-deposited area;

[[vias]] via holes are made in the insulating layer which electrically connect the semiconductor-surface-electrodes and the mount-surface-electrodes, the via holes are filled with solder or electric conductive paste;

the semiconductor-surface-electrodes, the insulating layer, and the mount-surface-electrodes are built up in this order on one side of the deposited semiconductor layers; and

a surface of the other side of the deposited semiconductor layers is a light emitting surface which emits light beams directly to outside from the semiconductor layers.

Claim 2. (Original) The light-emitting device of claim 1, wherein the insulating layer is made of one of resin, ceramics, or silicon.

Claim 3. (Canceled)

Claim 4. (Previously Presented) The light-emitting device of claim 1, wherein phosphor is provided on a surface or in an interior portion of the semiconductor layer.

Claim 5. – Claim 18. (Canceled)